

IGBT with Trench and Field-Stop technology

WGD15A65STFA3

Features

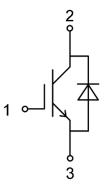
- V_{CES}=650V
- Ic=15A@Tc=100℃
- High efficient turn-on di/dt controllability
- Low V_{CE(sat)} enable high efficiencies
- Low Turn-off switching loss
- Very Good EMI and High Short-Circuit Ruggedness
- Packaging insulation
- RoSH Compliant
- Halogen free

Applications

- Motor Drives
- Home Appliance Applications
- Fan, Pumps, Vacuum Cleaner
- Other Hard Switching Applications



TO-220ISO









Package nin definition	1	2/Tab	3
Package pin definition	Gate	Collector	Emitter

Part	Package	Marking	Packing method	MPQ
WGD15A65STFA3	TO-220ISO	15A65STFA3	Tube	50/Tube



1 Maximum Ratings

Table 1 Maximum rated Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Values	Unit
Collector to Emitter Voltage	V _{CES}		650	V
Gate to Emitter Voltage	V _{GES}		±20	V
Continuous Collector Current			30	А
Continuous Collector Current	I _C	T _C =100℃	15	А
Pulsed Collector Current ¹	I _{CM}		60	Α
Diode Continuous Forward Current			30	А
Diode Continuous Forward Current	l _F ·	T _C =100℃	15	А
Diode Maximum Forward Current ¹	I _{FM}		60	Α
Maximum Dawar Dissination	P _{tot}		100	W
Maximum Power Dissipation		T _C =100℃	50	W
Operating Junction Temperature Range	TJ		-55~+175	°C
Storage Temperature Range	T _{STG}		-55~+150	$^{\circ}$
Thermal Resistance, Junction to case for IGBT	R _{th(J-C)}		1.5	K/W
Thermal Resistance, Junction to case for Diode	R _{th(J-C)}		2.8	K/W

Notes:

1. Pulse width limited by maximum junction temperature.





2 Electrical Characteristics, IGBT

Table 2 Characteristics Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Collector to Emitter Breakdown Voltage	BVces	I _C =250µA, V _{GE} =0V	650	-	-	V
	VCE(sat)	I _C =15A, V _{GE} =15V	-	1.73	2.30	V
Collector to Emitter Saturation Voltage		I _C =15A, V _{GE} =15V, T _J =150°C	-	2.10	-	V
Gate Threshold Voltage	V _{GE(th)}	Ic=250µA, V _{GE} =V _{CE}	4.5	5.5	6.5	V
Zero Gate Voltage Collector current	Ices	V _{CE} =650V, V _{GE} =0V	-	-	50	μA
Gate to Emitter Leakage Current	I _{GES}	V _{GE} =±20V, V _{CE} =0V	-	-	±100	nA
Internal Gate Resistor	R _{Gint}	f=1MHz, V _{AC} =25mV	-	10.0	-	Ω
Input Capacitance	Cies		-	1057	-	pF
Output Capacitance	Coes	f=1MHz, V _{CE} =25V, V _{GE} =0V	-	67	-	pF
Reverse Transfer Capacitance	Cres		-	22	-	pF
Total Gate charge	Q _G	V _{CC} =520V, I _C =15A, V _{GE} =15V	-	54	-	nc
Gate to Emiter charge	QGE		-	5	-	nc
Gate to Collector charge	Q _{GC}		-	33	-	nc
Short Circuit Withstand Time	tsc	V _{CC} =400V, V _{GE} =15V	-	5	-	μs
Turn-on Delay Time	t _{d(on)}		-	54	-	ns
Rising Time	t _r	V_{CC} =400V, I_{C} =15A, V_{GE} =0/15V, R_{G} =20 Ω , T_{J} =25°C Inductive load	-	44	-	ns
Turn-off Delay Time	t _{d(off)}		-	134	-	ns
Falling Time	t _f		-	80	-	ns
Turn-on Switching Loss Energy	Eon		-	0.28	-	mJ
Turn-off Switching Loss Energy	E _{off}		-	0.27	-	mJ
Turn-on Delay Time	t _{d(on)}		-	50	-	ns
Rising Time	tr	V _{CC} =400V, I _C =15A, V _{GE} =0/15V,	-	42	-	ns
Turn-off Delay Time	t _{d(off)}		-	146	-	ns
Falling Time	t _f	R _G =20Ω, T _J =150°C	-	128	-	ns
Turn-on Switching Loss Energy	Eon	Inductive load	-	0.50	-	mJ
Turn-off Switching Loss Energy	E _{off}		-	0.36	-	mJ





3 Electrical Characteristics, Diode

Table 3 Characteristics Values(T_c=25℃ unless otherwise specified)

Parameter	Symbol	Condition	Min.	Тур.	Max.	Unit
Forward Voltage	.,,	I⊧=15A, TJ=25°C	-	1.56	2.10	V
	V _F	I⊧=15A, Tյ=150°C	-	1.20	-	V
Peak Reverse Recovery Current	Irr	I⊧=15A di⊧/dt=-300A/μs Vcc=400V TJ=25°C	-	8	-	А
Reverse Recovery Time	t _{rr}		-	52	-	ns
Reverse Recovery Charge	Qrr		-	225	-	nC
Reverse Recovery Energy	Erec		-	52	-	μJ
Peak Reverse Recovery Current	Irr	I _F =15A di _F /dt=-300A/µs V _{CC} =400V TJ=150°C	-	12	-	А
Reverse Recovery Time	t _{rr}		-	96	-	ns
Reverse Recovery Charge	Qrr		-	678	-	nC
Reverse Recovery Energy	Erec		-	126	-	μJ





4 Typical Characteristics diagrams

Fig.1 Typical output characteristic $I_C=f(V_{CE}), T_{vi}=25^{\circ}C$

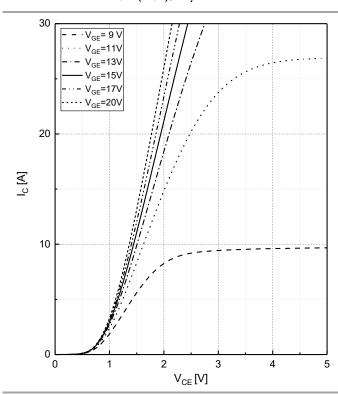


Fig.2 Typical output characteristic $I_C=f(V_{CE}), T_{vi}=150^{\circ}C$

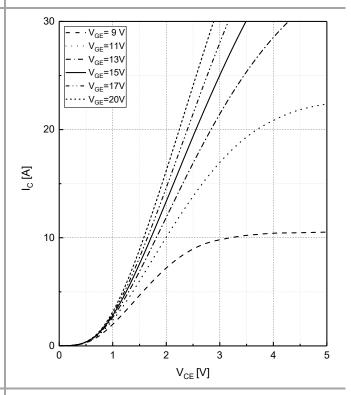
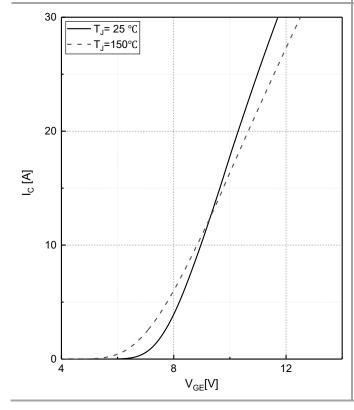


Fig.3 Typical transfer characteristic $I_C=f(V_{GE}), V_{CE}=20V$

Fig.4 Typical I_F as a function of V_F $I_F=f(V_F)$



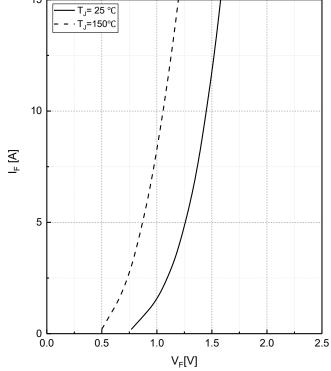
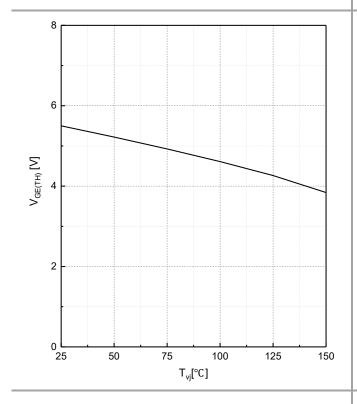




Fig.5 Typical $V_{GE(th)}$ as a function of T_{vj} V_{GEth} = $f(T_{vj})$, I_C =250 μ A

Fig.6 Typical V_{CEsat} as a function of T_{vj} $V_{CEsat}=f(T_{vj}), V_{GE}=15V$



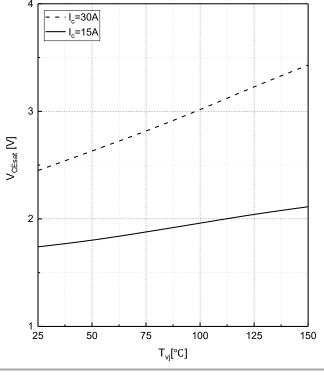
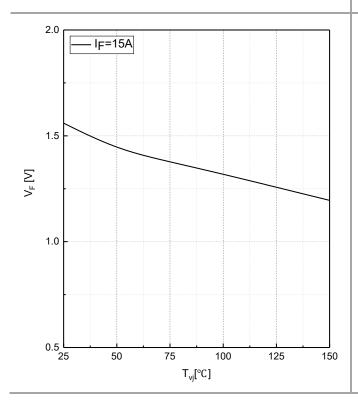


Fig.7 Typical V_F as a function of T_{vj} $V_F = f(T_{vj})$

Fig.8 Typical switching loss energy as a function of $R_{\rm G}$

 $E=f(R_G)$, $V_{CC}=400V$, $I_C=15A$, $V_{GE}=0/15V$, $T_J=150$ °C



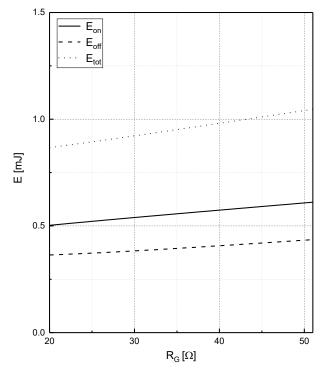
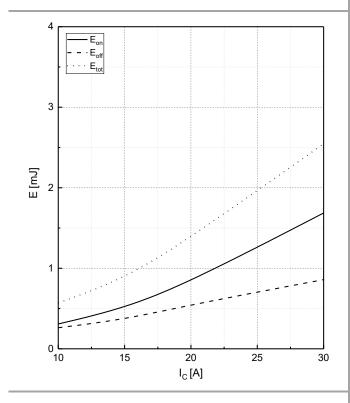




Fig.9 Typical switching loss energy as a function of I_{C}

 $E=f(I_C)$, $V_{CC}=400V$, $R_G=20\Omega$, $V_{GE}=0/15V$, $T_J=150^{\circ}C$

Fig.10 Typical Gate charge V_{GE} =f(Q_G), I_C=15A



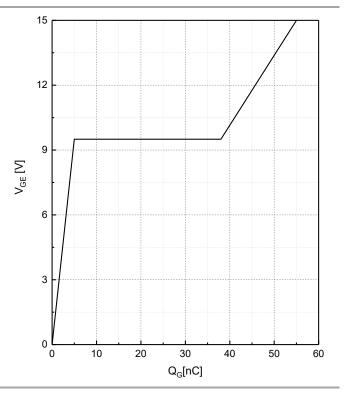
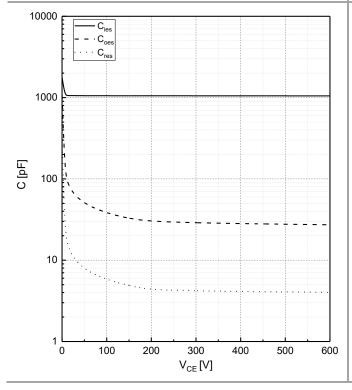


Fig.11 Typical capacitance as a function of V_{CE} C=f(V_{CE}), f=1MHz, V_{GE} =0V

Fig.12 Power dissipation as a function of T_C $P_{tot}=f(T_C), T_{vi} \le 175 ^{\circ}C$



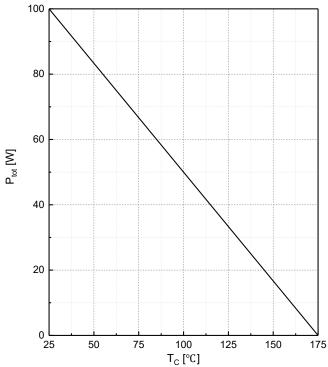
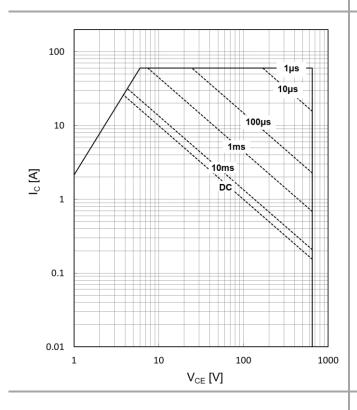




Fig.13 Forward bias safe operating area of IGBT $T_c=25^{\circ}\text{C}, T_{vi}\leq175^{\circ}\text{C}, V_{GE}=15\text{V}$

Fig.14 Transient thermal impedance of IGBT $Z_{th(j-c)} \! = \! f(t_p), \ D \! = \! t_p/T$



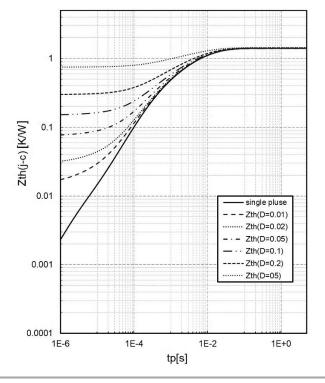
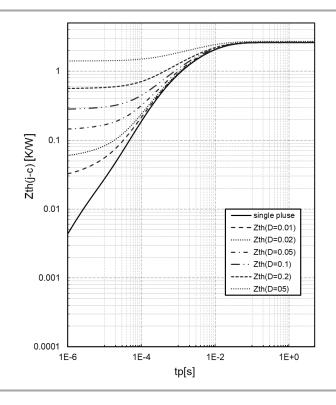


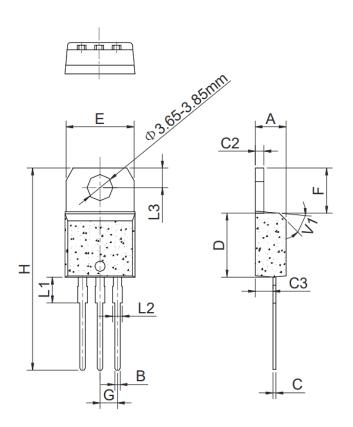
Fig.15 Transient thermal impedance of Diode $Z_{th(j-c)}=f(t_p),\ D=t_p/T$







5 Package Outlines



C)/MDCI	MM		
SYMBOL	MIN	MAX	
Α	4.40	4.60	
В	0.61	0.88	
С	0.46	0.70	
C2	1.21	1.32	
C3	2.40	2.72	
D	8.60	9.70	
E	9.80	10.40	
F	6.55	6.95	
G	2.40	2.70	
Н	28.0	29.8	
L1	3.75 REF		
L2	1.14	1.70	
L3	2.65	2.95	
V1	45° REF		

Contact Information

No.1001, Shiwan(7) Road, Pudong District, Shanghai, P.R.China.201202 Tel: 86-21-50310888 Fax: 86-21-50757680 Email: market@way-on.com

WAYON website: http://www.way-on.com

For additional information, please contact your local Sales Representative.

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Product Specification Statement

1. The product specification aims to provide users with a reference regarding various product parameters, performance, and usage. It presents certain aspects of the product's performance in graphical form and is intended solely for users to select product and make product comparisons, enabling users to better understand and evaluate the characteristics and advantages of the product. It does not constitute any commitment, warranty, or guarantee.

2.The product parameters described in the product specification are numerical values, characteristics, and functions obtained through actual testing or theoretical calculations of the product in an independent or ideal state. Due to the complexity of product applications and variations in test conditions and equipment, there may be slight fluctuations in parameter test values. WAYON shall not guarantee that the actual performance of the product when installed in the customer's system or equipment will be entirely consistent with the product specification, especially concerning dynamic parameters. It is recommended that users consult with professionals for product selection and system design. Users should also thoroughly validate and assess whether the actual parameters and performance when installed in their respective systems or equipment meet their requirements or expectations. Additionally, users should exercise caution in verifying product compatibility issues, and WAYON assumes no responsibility for the application of the product.

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4.Users are advised to pay attention to the parameter limit values specified in the product specification and maintain a certain margin in design or application to ensure that the product does not exceed the parameter limit values defined in the product specification. This precaution should be taken to avoid exceeding one or more of the limit values, which may result in permanent irreversible damage to the product, ultimately affecting the quality and reliability of the system or equipment.

5. The design of the product is intended to meet civilian needs and is not guaranteed for use in harsh environments or precision equipment. It is not recommended for use in systems or equipment such as medical devices, aircraft, nuclear power, and similar systems, where failures in these systems or equipment could reasonably be expected to result in personal injury. WAYON shall assume no responsibility for any consequences resulting from such usage.

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